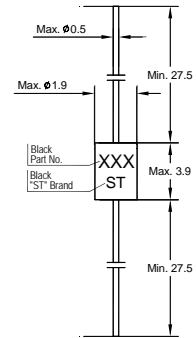


DB3, DB4, DC34

SILICON BIDIRECTIONAL DIACS

The glass passivated, three-layer, two terminal, axial lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current. These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.



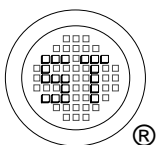
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation ($T_a = 65\text{ }^\circ\text{C}$)	P_{tot}	150	mW
Repetitive Peak On-state Current ($t_p = 20\text{ }\mu\text{s}$, $f = 100\text{ Hz}$)	I_{TRM}	2	A
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 40 to + 125	$^\circ\text{C}$

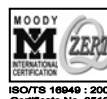
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Breakover Voltage	$V_{(\text{BR})1}$ and $V_{(\text{BR})2}$	28	36	V
		30	38	
		35	45	
Breakover Currents	$I_{(\text{BR})1}$ and $I_{(\text{BR})2}$	-	200	μA
Breakover Voltage Symmetry	$ V_{(\text{BR})1} - V_{(\text{BR})2} $	-	3.8	V
Dynamic Breakover Voltage $\Delta I = [I_{\text{BR}} \text{ to } I_F = 10\text{ mA}]$	$ \Delta V \pm $	5	-	V



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DB3, DB4, DC34

Fig.1 : Power dissipation versus ambient temperature (maximum values)

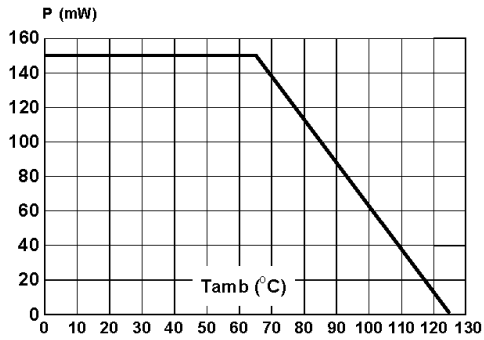


Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

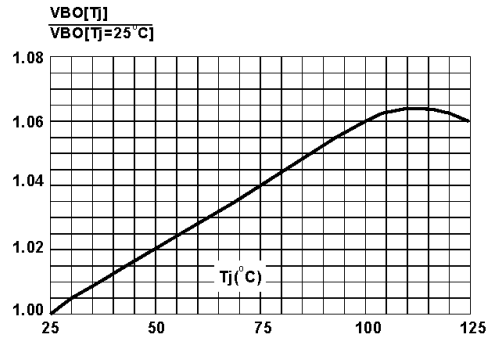
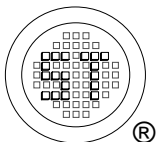
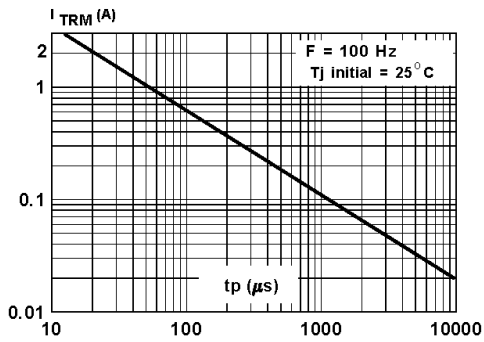


Fig.3 : Peak pulse current versus pulse duration (maximum values)



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